

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0132

2. Structure :

- 2-1. Type : P on N diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

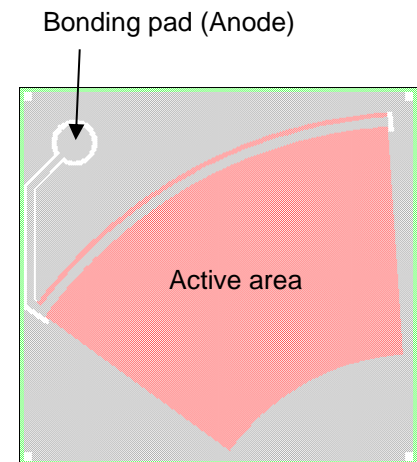
3. Size :

- 3-1. Chip size(including scribe lane) : 135.45 mils x 128.5 mils (3.4405 mm x 3.264 mm).
- 3-2. Chip thickness : 15.7 ± 1.5 mils (0.400 ± 0.038 mm).
- 3-3. Bonding pad (Anode) : diameter 305um.
- 3-4. Pattern drawing : Refer to the attached drawing

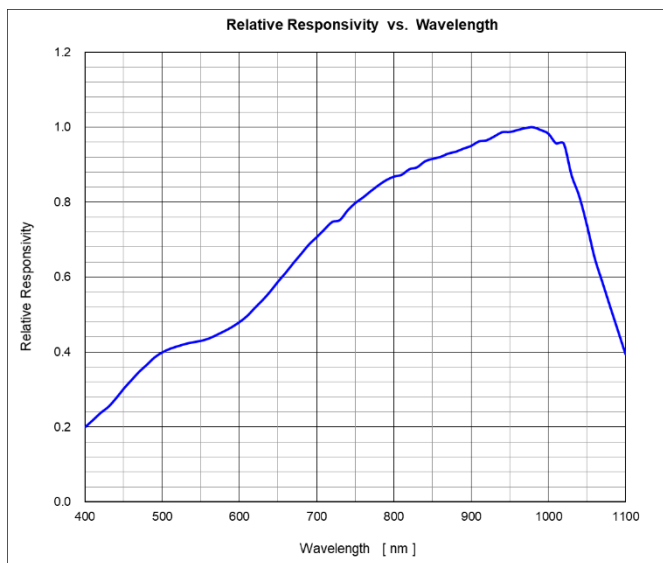
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	ID	VR=10V Ee=0mW/cm ²			20	nA
*Reverse breakdown voltage	V(BR)R	IR=100uA Ee=0mW/cm ²	30			V
*Forward voltage	VF	IF=20mA			1.3	V
Total Capacitance	Ct	VR =5V Ee=0mW/cm ² f=1MHz		88		pF

*Based on 100% probing



5. Relative spectral responsivity



*Bare chip measured with integrating sphere, for reference only.